an image signal line;

a pixel electrode; and

a thin film transistor comprising a gate electrode connected to the scanning signal line, a semiconductor film formed over the insulating film, a drain electrode electrically connected to the image signal line, and a source electrode electrically connected to the pixel electrode,

wherein the scanning signal line comprises a first metal film and an aluminum film formed over the first metal film, the aluminum film having an upper surface with a width that is smaller than a width of a lower surface of the first metal film.

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21. (Amended) A display device comprising:

a substrate;

a scanning signal line;

an insulating film formed over the substrate;

an image signal line;

a pixel electrode; and

a thin film transistor comprising a gate electrode connected to the scanning signal line and formed between the substrate and the insulating film, a semiconductor film formed over the insulating film, a drain electrode electrically connected to the image signal line, and a source electrode electrically connected to the pixel electrode,

wherein the drain electrode and the source electrode comprise a high melting point metal film and an aluminum film formed over the high melting point metal film, and

wherein the gate electrode and the scanning signal line comprise an aluminum film, and the scanning signal line has an upper surface with a width that is smaller than a width of a lower surface of the scanning signal line.

22. (Amended) A display device comprising:

a substrate;

a scanning signal line;

an insulating film formed over the substrate;

an image signal line;

a pixel electrode; and

a thin film transistor comprising a gate electrode connected to the scanning signal line and formed between the substrate and the insulating film, a semiconductor film formed over the insulating film, a drain electrode electrically connected to the image signal line, and a source electrode electrically connected to the pixel electrode,

wherein the drain electrode and the source electrode comprise a high melting point metal film and an aluminum film formed over the high melting point metal film, and the high melting point metal film and the aluminum film of both the source and drain electrodes are disposed such that a spacing between a lower surface of the high melting point metal film of the drain electrode and a lower surface of the high melting point metal film of the source electrode over the semiconductor film is smaller than a spacing between an upper surface of the aluminum film of the drain electrode and an upper surface of the aluminum film of the source electrode over the semiconductor film, and

wherein the gate electrode and the scanning signal line comprise an

aluminum film, and the scanning signal line having an upper surface with a width that is smaller than a width of a lower surface of the scanning signal line.